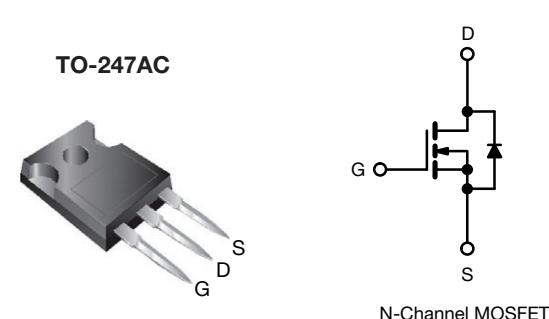


EF Series Power MOSFET With Fast Body Diode



FEATURES

- Low figure-of-merit (FOM) $R_{on} \times Q_g$
- Low input capacitance (C_{iss})
- Reduced switching and conduction losses
- Ultra low gate charge (Q_g)
- Avalanche energy rated (UIS)
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



RoHS
COMPLIANT
HALOGEN
FREE

APPLICATIONS

- Server and telecom power supplies
- Switch mode power supplies (SMPS)
- Power factor correction power supplies (PFC)
- Lighting
 - High-intensity discharge (HID)
 - Fluorescent ballast lighting
- Industrial
 - Welding
 - Induction heating
 - Motor drives
 - Battery chargers
 - Renewable energy
 - Solar (PV inverters)

PRODUCT SUMMARY	
V_{DS} (V) at T_J max.	650
$R_{DS(on)}$ typ. (Ω) at 25 °C	$V_{GS} = 10$ V 0.028
Q_g max. (nC)	400
Q_{gs} (nC)	43
Q_{gd} (nC)	143
Configuration	Single

ORDERING INFORMATION			
Package	TO-247AC		
Lead (Pb)-free and halogen-free	SiHG80N60EF-GE3		

ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)				
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-source voltage		V_{DS}	600	V
Gate-source voltage		V_{GS}	± 30	
Continuous drain current ($T_J = 150$ °C)	V_{GS} at 10 V	I_D	80	A
	$T_C = 25$ °C		51	
Pulsed drain current ^a		I_{DM}	254	
Linear derating factor			4.2	W/°C
Single pulse avalanche energy ^b		E_{AS}	1142	mJ
Maximum power dissipation		P_D	520	W
Operating junction and storage temperature range		T_J, T_{stg}	-55 to +150	°C
Drain-source voltage slope	$T_J = 125$ °C	dv/dt	70	V/ns
Reverse diode dv/dt ^d			50	
Soldering recommendations (peak temperature) ^c	For 10 s		260	°C

Notes

- Repetitive rating; pulse width limited by maximum junction temperature
- $V_{DD} = 140$ V, starting $T_J = 25$ °C, $L = 28.2$ mH, $R_g = 25$ Ω, $I_{AS} = 9.0$ A
- 1.6 mm from case
- $I_{SD} \leq I_D$, $di/dt = 100$ A/μs, starting $T_J = 25$ °C

THERMAL RESISTANCE RATINGS

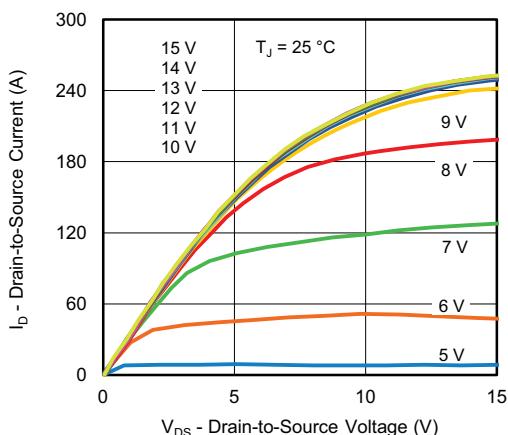
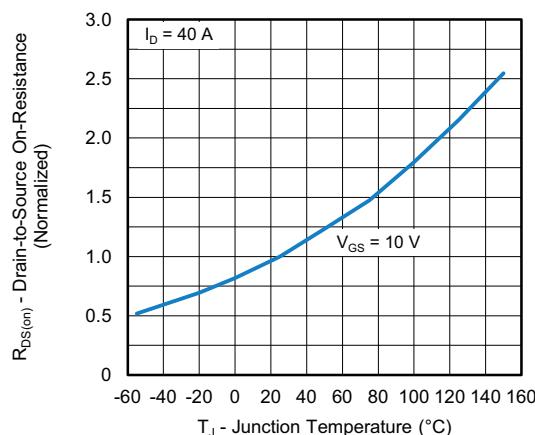
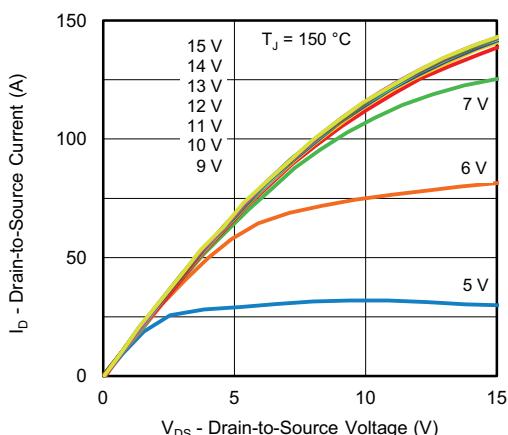
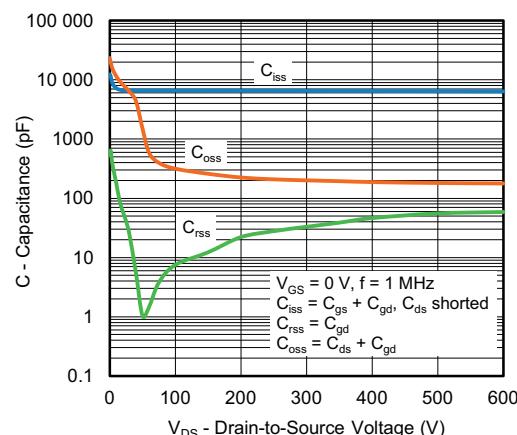
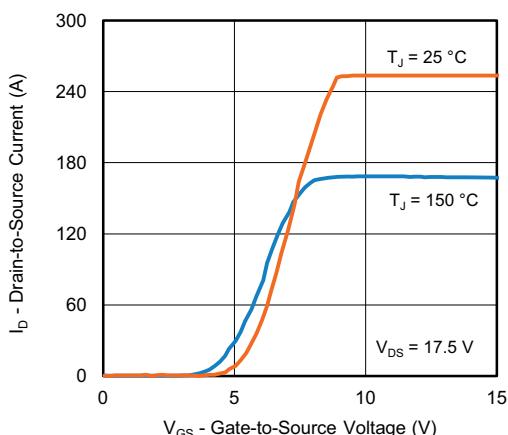
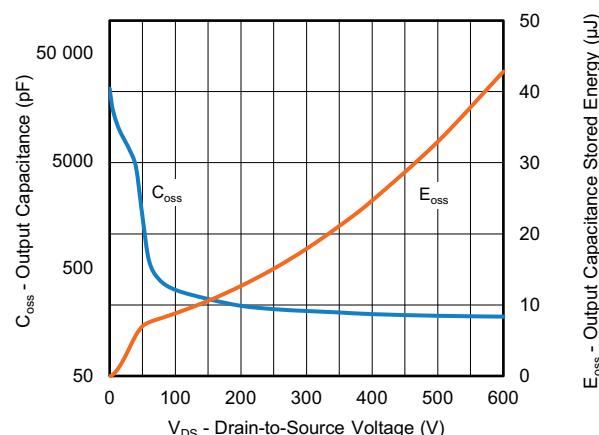
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum junction-to-ambient	R_{thJA}	-	40	
Maximum junction-to-case (drain)	R_{thJC}	-	0.24	°C/W

SPECIFICATIONS (T_J = 25 °C, unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-source breakdown voltage	V_{DS}	$V_{GS} = 0 \text{ V}$, $I_D = 250 \mu\text{A}$		600	-	-	V
V_{DS} temperature coefficient	$\Delta V_{DS}/T_J$	Reference to 25 °C, $I_D = 10 \text{ mA}$		-	0.65	-	V/°C
Gate-source threshold voltage (N)	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250 \mu\text{A}$		2.0	-	4.0	V
Gate-source leakage	I_{GSS}	$V_{GS} = \pm 20 \text{ V}$		-	-	± 100	nA
		$V_{GS} = \pm 30 \text{ V}$		-	-	± 1	μA
Zero gate voltage drain current	I_{DSS}	$V_{DS} = 480 \text{ V}$, $V_{GS} = 0 \text{ V}$		-	-	1	
		$V_{DS} = 480 \text{ V}$, $V_{GS} = 0 \text{ V}$, $T_J = 125 \text{ °C}$		-	-	500	μA
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS} = 10 \text{ V}$	$I_D = 40 \text{ A}$	-	0.028	0.032	Ω
Forward transconductance ^a	g_{fs}	$V_{DS} = 30 \text{ V}$, $I_D = 40 \text{ A}$		-	25	-	S
Dynamic							
Input capacitance	C_{iss}	$V_{GS} = 0 \text{ V}$, $V_{DS} = 100 \text{ V}$, $f = 1 \text{ MHz}$		-	6600	-	pF
Output capacitance	C_{oss}			-	320	-	
Reverse transfer capacitance	C_{rss}			-	8	-	
Effective output capacitance, energy related ^a	$C_{o(er)}$	$V_{DS} = 0 \text{ V}$ to 480 V, $V_{GS} = 0 \text{ V}$		-	214	-	pF
Effective output capacitance, time related ^b	$C_{o(tr)}$			-	1051	-	
Total gate charge	Q_g			-	266	400	nC
Gate-source charge	Q_{gs}	$V_{GS} = 10 \text{ V}$	$I_D = 40 \text{ A}$, $V_{DS} = 480 \text{ V}$	-	43	-	
Gate-drain charge	Q_{gd}			-	143	-	
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 480 \text{ V}$, $I_D = 40 \text{ A}$, $V_{GS} = 10 \text{ V}$, $R_g = 9.1 \Omega$		-	59	89	ns
Rise time	t_r			-	144	216	
Turn-off delay time	$t_{d(off)}$			-	272	408	
Fall time	t_f			-	168	252	
Gate input resistance	R_g	$f = 1 \text{ MHz}$, open drain		0.6	1.2	2.4	Ω
Drain-Source Body Diode Characteristics							
Continuous source-drain diode current	I_S	MOSFET symbol showing the integral reverse p - n junction diode		-	-	80	A
Pulsed diode forward current	I_{SM}			-	-	254	
Diode forward voltage	V_{SD}	$T_J = 25 \text{ °C}$, $I_S = 40 \text{ A}$, $V_{GS} = 0 \text{ V}$		-	-	1.2	V
Reverse recovery time	t_{rr}	$T_J = 25 \text{ °C}$, $I_F = I_S = 40 \text{ A}$, $di/dt = 100 \text{ A}/\mu\text{s}$, $V_R = 400 \text{ V}$		-	206	412	ns
Reverse recovery charge	Q_{rr}			-	1.9	3.8	μC
Reverse recovery current	I_{RRM}			-	18	-	A

Notes

a. $C_{oss(er)}$ is a fixed capacitance that gives the same energy as C_{oss} while V_{DS} is rising from 0 % to 80 % V_{DSS}
b. $C_{oss(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 % to 80 % V_{DSS}

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Fig. 1 - Typical Output Characteristics

Fig. 4 - Normalized On-Resistance vs. Temperature

Fig. 2 - Typical Output Characteristics

Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

Fig. 3 - Typical Transfer Characteristics

Fig. 6 - C_{oss} and E_{oss} vs. V_{DS}

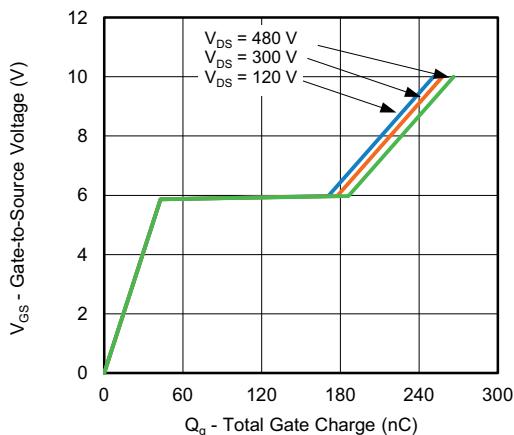


Fig. 7 - Typical Gate Charge vs. Gate-to-Source Voltage

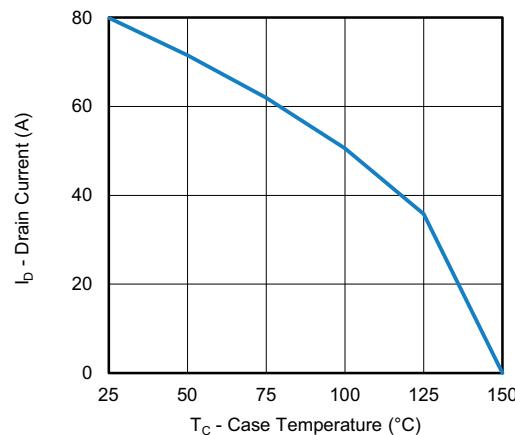


Fig. 10 - Maximum Drain Current vs. Case Temperature

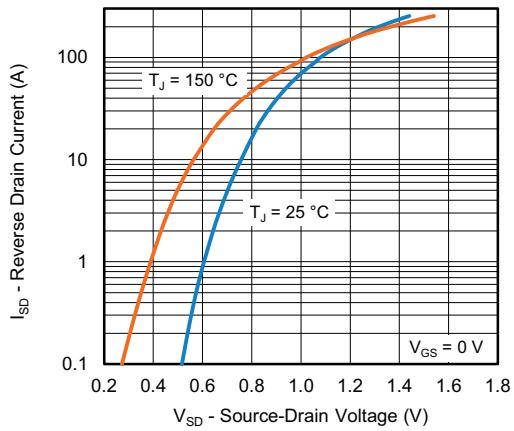


Fig. 8 - Typical Source-Drain Diode Forward Voltage

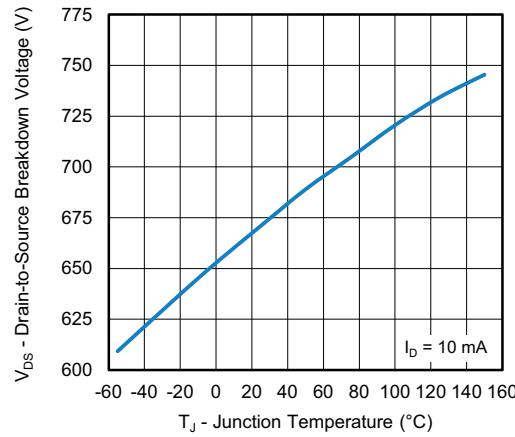


Fig. 11 - Temperature vs. Drain-to-Source Voltage

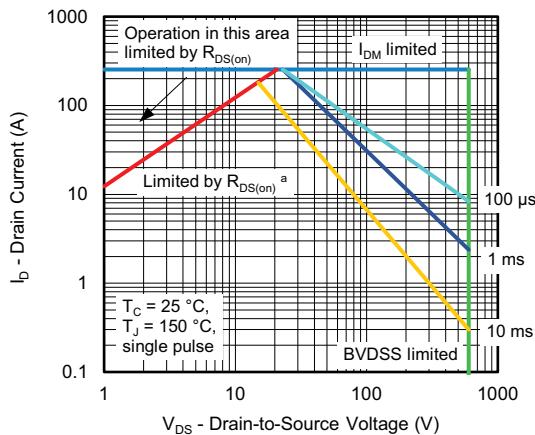


Fig. 9 - Maximum Safe Operating Area

Note

a. $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

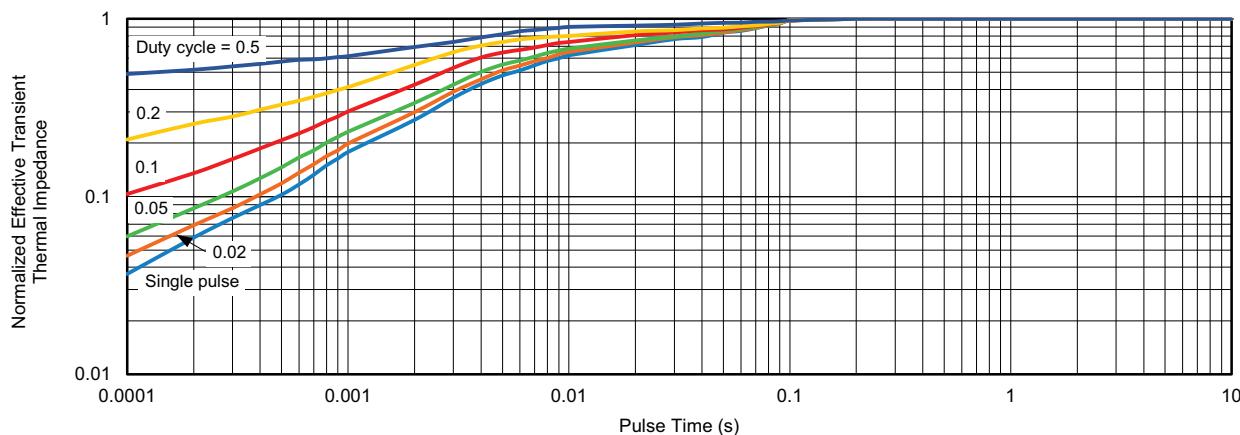


Fig. 12 - Normalized Transient Thermal Impedance, Junction-to-Case

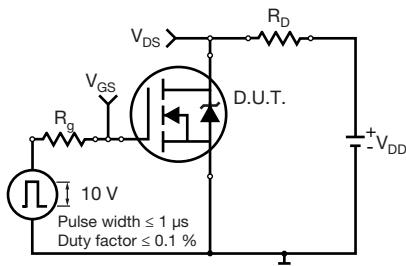


Fig. 13 - Switching Time Test Circuit

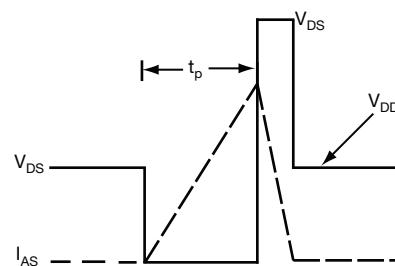


Fig. 16 - Unclamped Inductive Waveforms

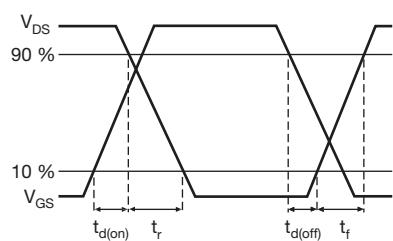


Fig. 14 - Switching Time Waveforms

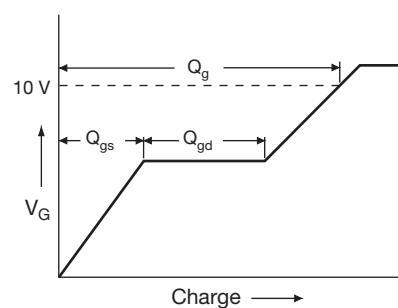


Fig. 17 - Basic Gate Charge Waveform

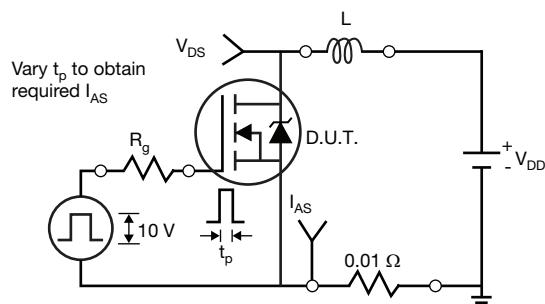


Fig. 15 - Unclamped Inductive Test Circuit

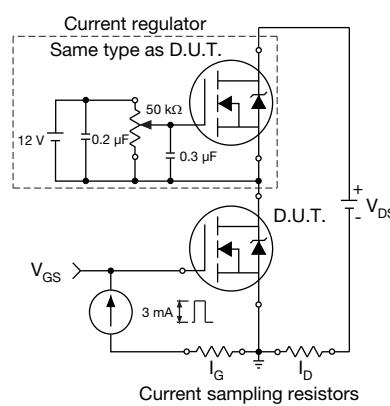


Fig. 18 - Gate Charge Test Circuit

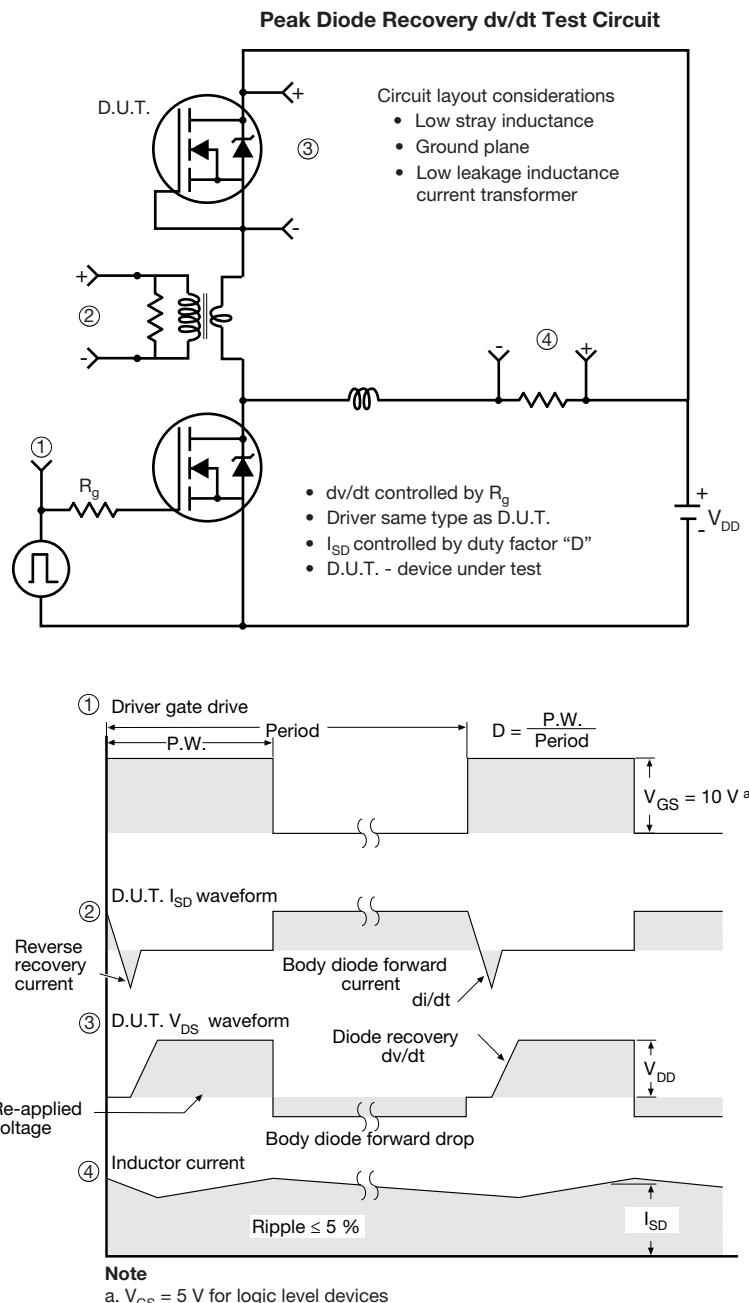
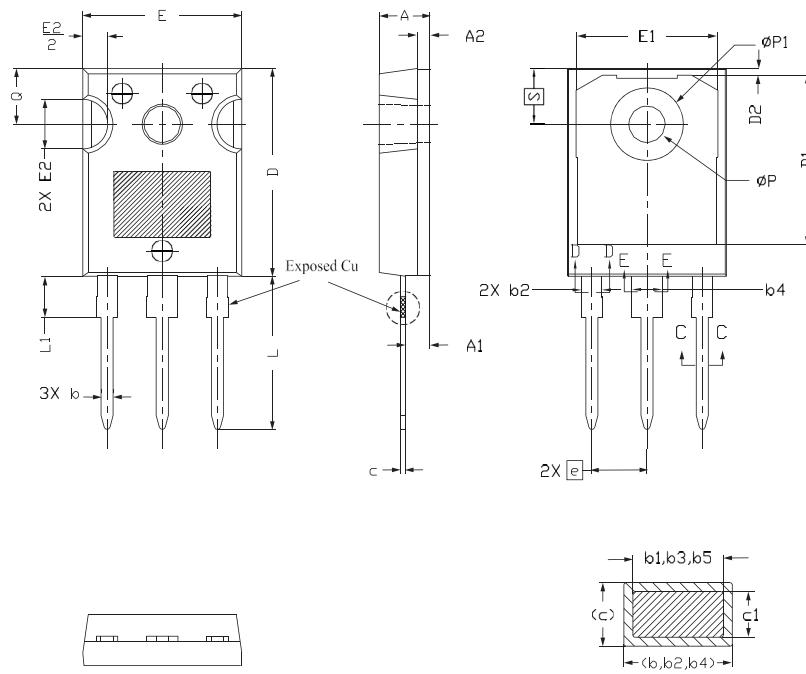


Fig. 19 - For N-Channel

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TO-247AC (High Voltage)

VERSION 1: FACILITY CODE = 9



Section C-C,D-D,E-E

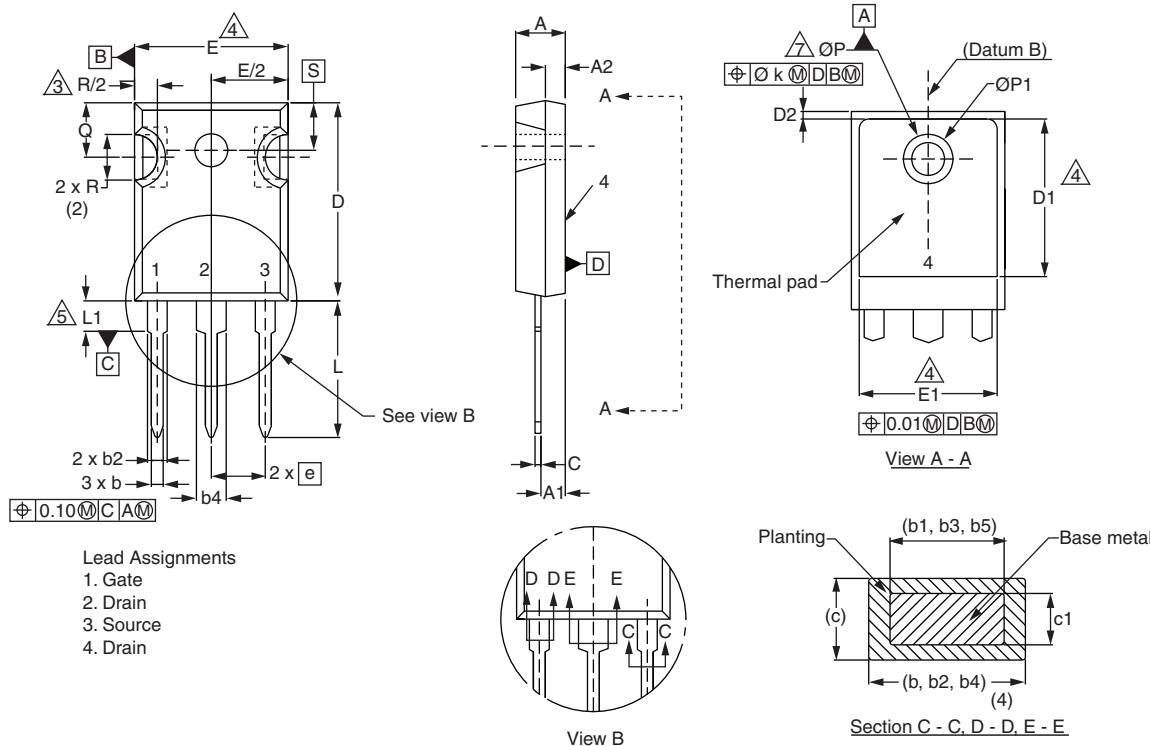
MILLIMETERS				
DIM.	MIN.	NOM.	MAX.	NOTES
A	4.83	5.02	5.21	
A1	2.29	2.41	2.55	
A2	1.17	1.27	1.37	
b	1.12	1.20	1.33	
b1	1.12	1.20	1.28	
b2	1.91	2.00	2.39	6
b3	1.91	2.00	2.34	
b4	2.87	3.00	3.22	6, 8
b5	2.87	3.00	3.18	
c	0.40	0.50	0.60	6
c1	0.40	0.50	0.56	
D	20.40	20.55	20.70	4

Notes

- (1) Package reference: JEDEC® TO247, variation AC
- (2) All dimensions are in mm
- (3) Slot required, notch may be rounded
- (4) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm per side. These dimensions are measured at the outermost extremes of the plastic body
- (5) Thermal pad contour optional with dimensions D1 and E1
- (6) Lead finish uncontrolled in L1
- (7) Ø P to have a maximum draft angle of 1.5° to the top of the part with a maximum hole diameter of 3.91 mm
- (8) Dimension b2 and b4 does not include dambar protrusion. Allowable dambar protrusion shall be 0.1 mm total in excess of b2 and b4 dimension at maximum material condition

MILLIMETERS				
DIM.	MIN.	NOM.	MAX.	NOTES
D1	16.46	16.76	17.06	5
D2	0.56	0.66	0.76	
E	15.50	15.70	15.87	4
E1	13.46	14.02	14.16	5
E2	4.52	4.91	5.49	3
e	5.46 BSC			
L	14.90	15.15	15.40	
L1	3.96	4.06	4.16	6
Ø P	3.56	3.61	3.65	7
Ø P1	7.19 ref.			
Q	5.31	5.50	5.69	
S	5.51 BSC			

VERSION 2: FACILITY CODE = Y



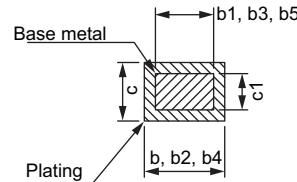
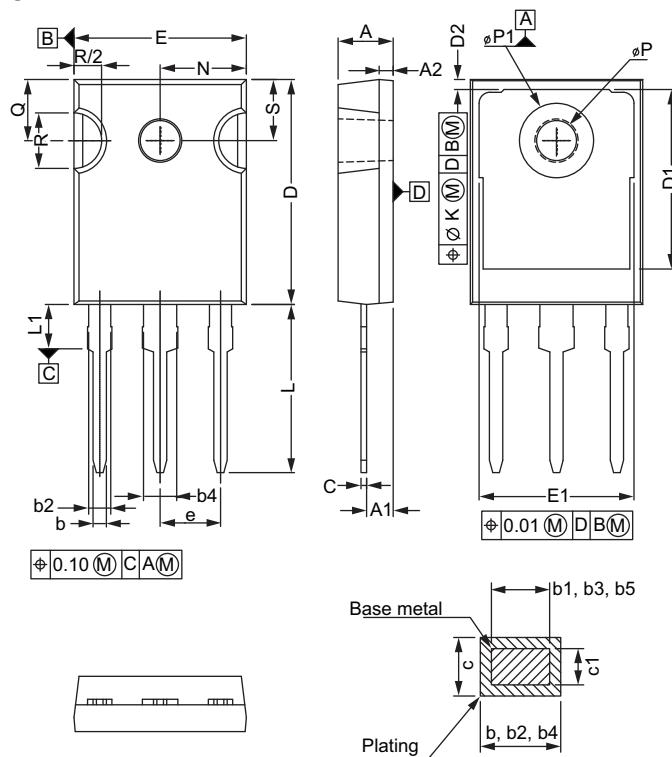
MILLIMETERS			
DIM.	MIN.	MAX.	NOTES
A	4.58	5.31	
A1	2.21	2.59	
A2	1.17	2.49	
b	0.99	1.40	
b1	0.99	1.35	
b2	1.53	2.39	
b3	1.65	2.37	
b4	2.42	3.43	
b5	2.59	3.38	
c	0.38	0.86	
c1	0.38	0.76	
D	19.71	20.82	
D1	13.08	-	

MILLIMETERS			
DIM.	MIN.	MAX.	NOTES
D2	0.51	1.30	
E	15.29	15.87	
E1	13.72	-	
e	5.46 BSC		
Ø k	0.254		
L	14.20	16.25	
L1	3.71	4.29	
Ø P	3.51	3.66	
Ø P1	-	7.39	
Q	5.31	5.69	
R	4.52	5.49	
S	5.51 BSC		

Notes

- (1) Dimensioning and tolerancing per ASME Y14.5M-1994
- (2) Contour of slot optional
- (3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Thermal pad contour optional with dimensions D1 and E1
- (5) Lead finish uncontrolled in L1
- (6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")
- (7) Outline conforms to JEDEC outline TO-247 with exception of dimension c

VERSION 3: FACILITY CODE = N



MILLIMETERS		
DIM.	MIN.	MAX.
A	4.65	5.31
A1	2.21	2.59
A2	1.17	1.37
b	0.99	1.40
b1	0.99	1.35
b2	1.65	2.39
b3	1.65	2.34
b4	2.59	3.43
b5	2.59	3.38
c	0.38	0.89
c1	0.38	0.84
D	19.71	20.70
D1	13.08	-

ECN: E22-0452-Rev. G, 31-Oct-2022

DWG: 5971

MILLIMETERS		
DIM.	MIN.	MAX.
D2	0.51	1.35
E	15.29	15.87
E1	13.46	-
e	5.46 BSC	
k	0.254	
L	14.20	16.10
L1	3.71	4.29
N	7.62 BSC	
P	3.56	3.66
P1	-	7.39
Q	5.31	5.69
R	4.52	5.49
S	5.51 BSC	

Notes

- (1) Dimensioning and tolerancing per ASME Y14.5M-1994
- (2) Contour of slot optional
- (3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Thermal pad contour optional with dimensions D1 and E1
- (5) Lead finish uncontrolled in L1
- (6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")

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